

C-TCT measurements on scCVD diamond and its use at CNGS

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Outline

Motivation and Concept

Why and how to investigate charge transport/collection at cold temperatures?

The Set-up

Why diamond? The experimental technique

Results and Model

Current pulses and what we can learn from them

Diamonds at CNGS

Motivation and Concept

- Understand charge transport over a wide temp. range:
 - Beam Loss Monitors within the LHC magnets
 - \rightarrow Operate detector at 1.9 K
 - Electrical Devices in space crafts
 - → Huge temperature range



- Perform transient current technique (TCT) at various controlled temperatures and field strengths:
 - → Provides a powerful technique for study of transport characteristics
- Analyse current pulses in terms of transit time, area, ...
 → compare data to model

Why Diamond

Pros:

- > High band gap (5.5 eV)
 - → Very high breakdown field > 1e7 V/cm
 - \rightarrow Very high resistivity > 1e11 Ω cm
 - → Large area
 - → Very low leakage current ~ few pA
- Low dielectric constant (5.7)
 → Low capacitance → Low noise
- ≻ High displacement energy (43 eV/atom)
 → Radiation hard → No replacement
- High mobility (~2000 cm²/Vs)
 - → Fast signals
 - \rightarrow High collision rate
- Very wide sensitivity range
 → Single MIP to few THz tested
- Wide operational temperature range



- High E_{pair-creation} (13.5 eV)
 → Less signal, but S2N-ratio comparable to Si
- Rather high costs
- Not as well understood as Si
 More R&D efforts needed



The Experimental Technique

- The Transient-Current Technique (TCT) measurement:
 - α particles impinge on top side
 Create eh-pairs close to electrode
 Electric field separates charges
 Drifting charges induce current
 - → measure the transient current
 - \rightarrow Pos. (neg.) bias \rightarrow Measure e⁻ (h⁺)
 - → Use fast (2 GHz), low noise (3 mV) current amplifier, 40 dB
 - \rightarrow record signal with oscilloscope



The Set-up I

Sensor + Sensor holder:



Sample size: 5x5 mm², 500 μm



• Circuit schematics:



The Cryostat

- Outer chamber:
 - liquid helium
 - pressure = 1 bar for $T \ge 4.2 \text{ K}$
 - pressure few mbar for T = 1.6 K
- inner vacuum chamber:
 - helium gas @ few 10⁻² mbar
 - where the sensor is
 - \rightarrow almost no energy loss of the α s
 - → high breakdown voltage
 - \rightarrow good thermalisation



TCT Pulses at RT: Holes



TCT Pulses at RT: Electrons



The Plasma



TCT Pulses at Various Temperatures



Verified for three samples, two metallisations !

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TCT Pulses at Various Temperatures



The Plasma again





- Always collect "outer" charge
- Fraction inner to outer
 → E-Field dependent
- "Inside": Thermal equilibrium between excitons and free e-h pairs
- Charges are released with $\tau_{evap} \sim \exp(E_{\chi}/kT)$
 - \rightarrow charges being retained, thermal lifetime 100 ps (RT) to 100 us
 - \rightarrow recombination time (~2ns) important for T < 150 K

The Model

- Creation of excitons and subsequent ionisation or ۲ recombination
- If ionised, charges are transported ۲



Analysis of TCT Pulses

• Calculate integral of pulse:



Integrated Charge

 Integrate n_{out}(t) over t, fit model to the integral of pulses over T :



Integrated Charge

• Charge as function of E-field:



- For T> 150 K:
 - Full charge at 300 V
 - Recombination leads to charge loss for |U| < 300V, why?
 - NO TRAPPING DURING! See flat pulses. Q-E behaviour not dominated by CCD ($\tau_{trap} \approx 1$ us)
 - This is charge recombination in the early plasma
 - -> Dominant charge loss mechanism in high-quality, unirradiated scCVD diamond
- For T < 80 K:
 - ALL inner charges recombine
 - only measure outer charges
 - See how "outer" part grows with field strength
 - -> sensitive to physical processes within first ~100 ps of the plasma!

Analysis of TCT Pulses

 Fit rectangular (2- Erfc(t)) – (2- Erfc(t-t')) + exponential (1-exp(-t/τ)) - (1 - exp(-(t-t')/τ))



Hole Drift Velocity



- μ_h increases with decreasing T down to 2 K
- $v_{sat} \sim constant$ with temperature @ 14e6 cm/s

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Mobility vs. Temperature



- Holes: For 300 K <T< 200K the mobility increases as acoustic phonon scattering decreases: $\alpha = -1.49$, $\mu_0 = 2400$ cm²/Vs
- 50 K to 10 K: mobility stays ~const.
 -> scattering dominated by neutral impurity scattering

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Saturation velocity



Holes: v_{sat} ~ constant with T , low T limit: 14e6 cm/s
 Electrons: v_{sat} has certain dependence, low T limit: 14e6 cm/s

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Temperature dependence of charge carrier mobility in single-crystal chemical vapour deposition diamond

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Comparison with Silicon



Conclusion from cold measurements

- Diamond detects radiation even at 2 K
- Charge collection is function of the temperature:
 - \rightarrow full charge at T > 150 K
 - → collection of 'outer charge only' for $T \le 75$ K
- Creation of excitons by alpha particles in the diamond
 - → maybe implications even at room temperature? Surface recombination, etc.
- First diamond mobility measurement down to 2 K
- Further reading:
 - H. Pernegger et al., JAP 97 (7) (2005) 073704.
 - C. Erginsoy, Phys. Rev. 79 (1950) 1013–1014
 - H. Jansen et al., Physics Procedia 37 (2012) 2005
 - H. Jansen et al., JAP 113 173706 (2013)

Usage of CVD Diamond at CNGS

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• Where?



• Where?



Connection from detectors to Control Room:



• TNM 41:





Poly-crystalline CVD diamond detectors:

- 8mm x 8mm
- 500 um thickness
- no amplification, direct scope read-out, 50 Ohm

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From Single Extraction:



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Intensity/Profile Measurements

Zoom:



 \rightarrow 5 ns bunch structure from SPS RF evident

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Compare p- to µ-beam structure

- Signals from BCT and DDs agree nicely
- Even local features show up in both DDs and BCTF



Verification of CNGS Timing

Measure delays between read-out windows



→ Calculate the Time-of-Flight:

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$$\text{ToF}_{\hat{\Theta}_x} = (6205.4 \pm 3.6) \text{ ns}$$

 $\text{ToF}_{\text{nom}} = \frac{1859.95 \text{ m}}{v} = (6205.3 \pm 2.5) \text{ ns}$

Conclusion

- Diamond is fast:
 - → Measure individual bunches up to \sim 200 MHz.
 - \rightarrow Usable as intensity monitor.
- Diamond is usable as cryogenic BLM, just keep in mind T-dependence of mobility and charge yield









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 Alpha-particles in WATER: avg. energy of secondary electrons is 60 eV



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The Plasma

The alpha-particle heats the ionisation volume!



 $C_v \sim T^3$

Analysis of TCT Pulses

 Fit rectangular (2- Erfc(t)) – (2- Erfc(t-t')) + exponential (1-exp(-t/τ)) - (1 - exp(-(t-t')/τ))



Analysis of TCT Pulses

Plot fitted τ a.f.o. temperature, and fit T-dependent model:



Comparison with Silicon



Excitons

Recombination via impurities



Cosmic Muons



- Use charge-sensitive amplifier here
- Charge degradation much less with MIPs
 - expected due to lower charge density!

Detailed set-up

overview





Common circuit for Diamond Detectors

 Diamond is a semi-conductor based, solid state ionization chamber:



Courtesy CIVIDEC Counting Mode

E

Calorimetric Mode



Courtesy CIVIDEC pCVD Diamond:

very short signal ~2ns FWHM @ 1V/um

optimal double pulse resolution charges lost at trapping centres

scCVD Diamond:

short signal ~5ns FWHM @ 1V/um

optimal Signal-to-Noise ratio lower trapping centre concentration

$$CCD = d * Q_{sig}/Q_{0}$$



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